

AMENDMENTS TO THE SPECIFICATION

Please replace lines 5-9 on page 7 with the following, as rewritten in amendment format:

Conditions such as pressure, microwave, O₂ gas, H₂N₂-N₂/H₂ gas, temperature as shown in Table 1 have been used for testing whether or not a popping has occurred. When a dopant contain P or As was used under a pressure of 1500mTorr, in a plasma power of 1500W, with 2000sccm of oxygen gas and with an amount of H₂N₂-N₂/H₂ gas ranging from 200sccm to 500sccm, no popping has occurred.

Please replace lines 18-23 on page 5 with the following, as rewritten in amendment format:

At the step of gas processing (300-3), a processing gas, including one or more of O₂, N₂, N₂/H₂, O₃ or CF₄, is introduced into the reaction chamber while the silicon substrate is put on a high-temperature hot plate to reach a level of pressure appropriate to the processing conditions, and then the pressure is maintained. The temperature change of the silicon plate during this procedure is as shown in Fig. 3. The processing gas used here may be the same as that used in a conventional ashing method.

Please replace lines 14-19 on page 3 with the following, as rewritten in amendment format:

In order to achieve the above objectives, the present invention provides an ashing method comprising a first step, wherein a silicon substrate, either pad-etched or via-etched, is in situ baked while it is put on a high-temperature hot plate, and a subsequent ashing step, wherein soft photoresists as well as hard photoresists are ashed simultaneously, using plasma. The present invention, being applicable to any photoresist ashing process, shows especially high efficiency with does ion implanted silicon substrates.